UNIKC Semiconductor

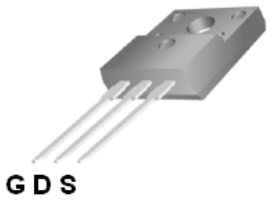
RoHS Compliant

P9006ETF

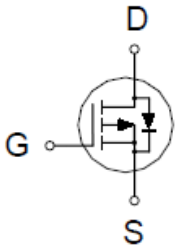
P-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-60	90mΩ @V_{GS} = 10V	-15A



TO-220F



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[1]	T_C = 25 °C	I_D	-15	A
	T_C = 100 °C		-9.5	
Pulsed Drain Current[2]		I_{DM}	-60	
Avalanche Current		I_{AS}	-24	
Avalanche Energy	L = 0.1mH	E_{AS}	28	mJ
Power Dissipation	T_C = 25 °C	P_D	35	W
	T_C = 100 °C		14	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3.6	°C / W
Junction-to-Ambient	$R_{\theta JA}$		60	

[1]Pulse width limited by maximum junction temperature.

[2]Limited by package.

UNIKC Semiconductor

RoHS Compliant

P9006ETF

P-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.0	-1.8	-3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -48V, V_{GS} = 0V			1	μA
		V_{DS} = -40V, V_{GS} = 0V , T_J = 125 °C			10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = -5V, V_{GS} = -10V	-60			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = -4.5V, I_D = -6A		79	135	mΩ
		V_{GS} = -10V, I_D = -18A		63	90	
Forward Transconductance[1]	g_{fs}	V_{DS} = -5V, I_D = -18A		20		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -25V, f = 1MHz		1130		pF
Output Capacitance	C_{oss}			129		
Reverse Transfer Capacitance	C_{rss}			81		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		4.85		Ω
Total Gate Charge[2]	Q_g	V_{DS} = 0.5$V_{(BR)DSS}$, V_{GS} = -10V, I_D = -18A		22.0		nC
Gate-Source Charge[2]	Q_{gs}			4.6		
Gate-Drain Charge[2]	Q_{gd}			5.5		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = -30V, $I_D \cong$ -18A, V_{GS} = -10V, R_{GS} = 6Ω		18		nS
Rise Time[2]	t_r			120		
Turn-Off Delay Time[2]	$t_{d(off)}$			20		
Fall Time[2]	t_f			58		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				-15	A
Forward Voltage[1]	V_{SD}	I_F = -18A, V_{GS} = 0V			-1.3	V
Reverse Recovery Time	t_{rr}	I_F = -18A, dI_F/dt = 100A / μS		71		nS
Reverse Recovery Charge	Q_{rr}			254		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

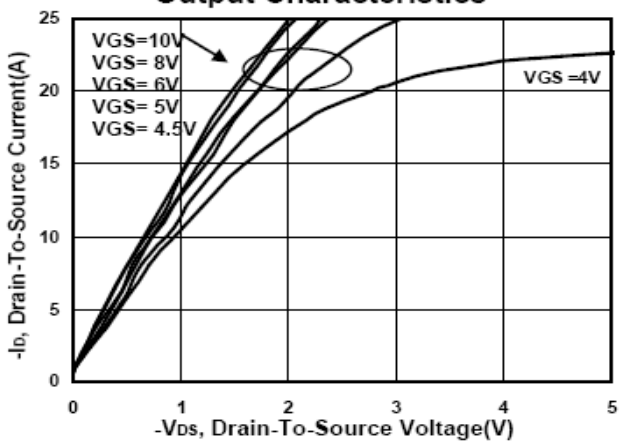
UNIKC Semiconductor

RoHS Compliant

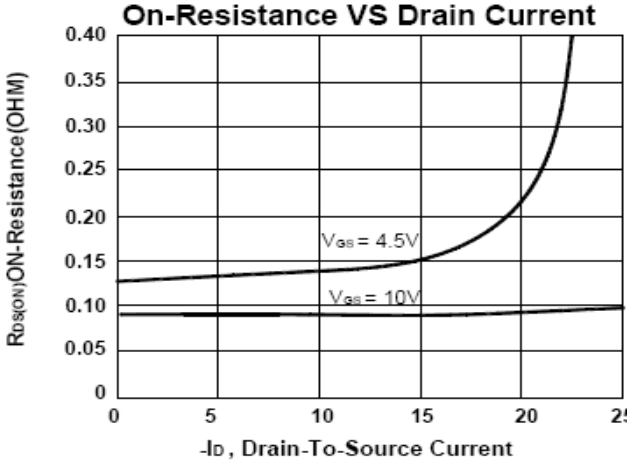
P9006ETF

P-Channel Enhancement Mode MOSFET

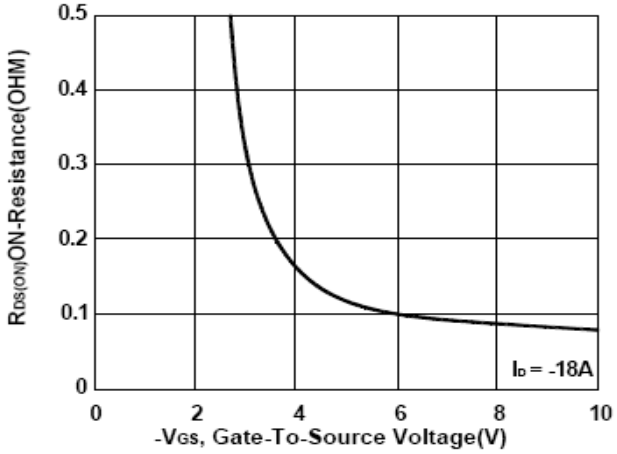
Output Characteristics



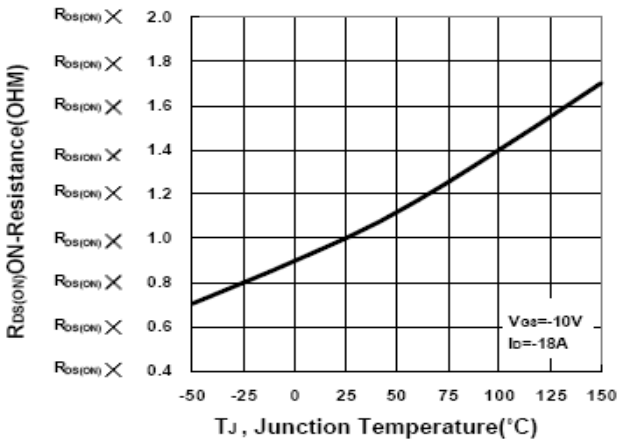
On-Resistance VS Drain Current



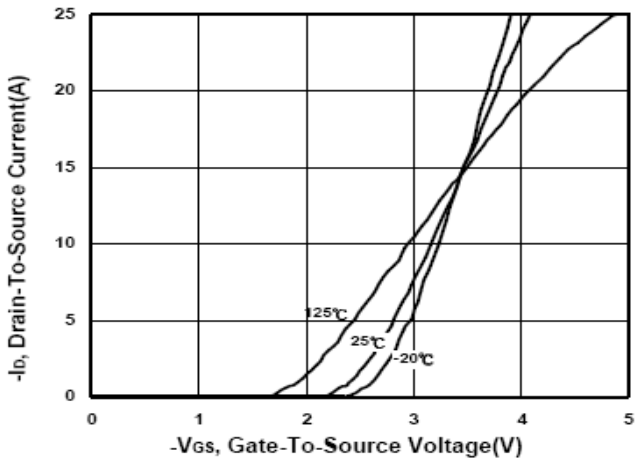
On-Resistance VS Gate-To-Source



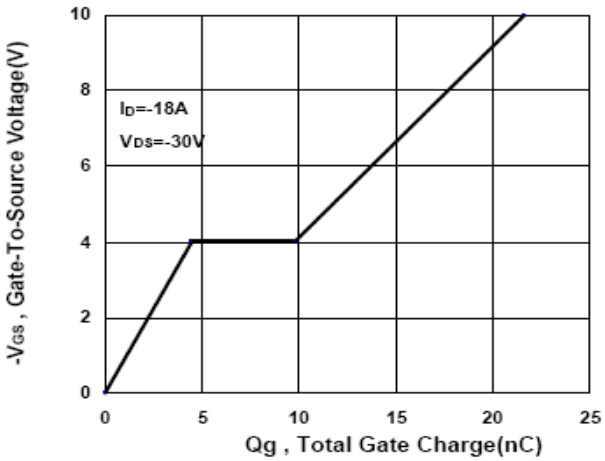
On-Resistance VS Temperature



Transfer Characteristics



Gate charge Characteristics



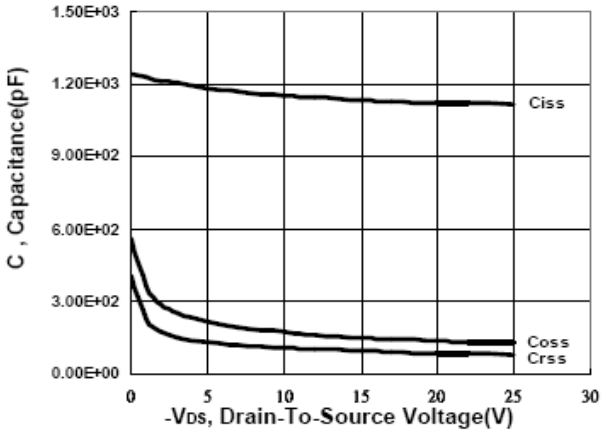
UNIKC Semiconductor

RoHS Compliant

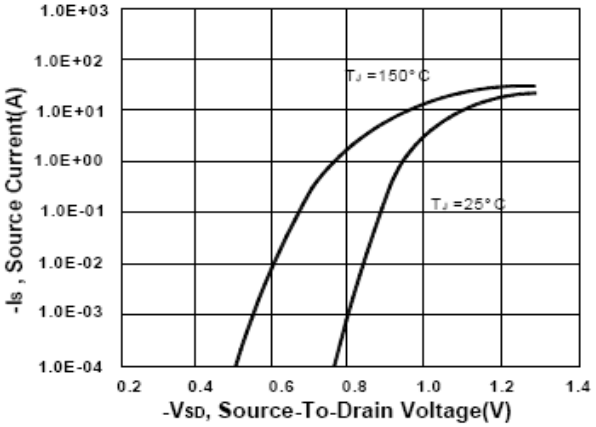
P9006ETF

P-Channel Enhancement Mode MOSFET

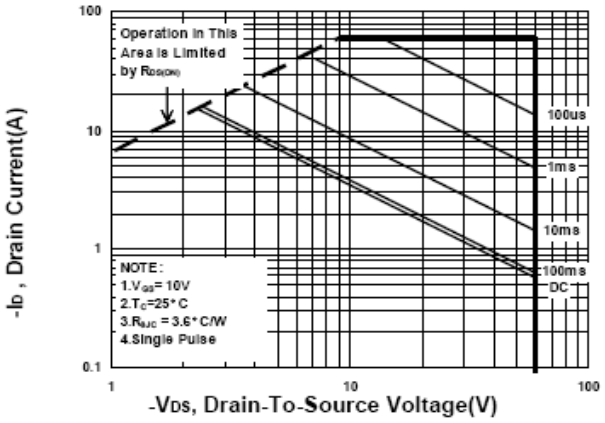
Capacitance Characteristic



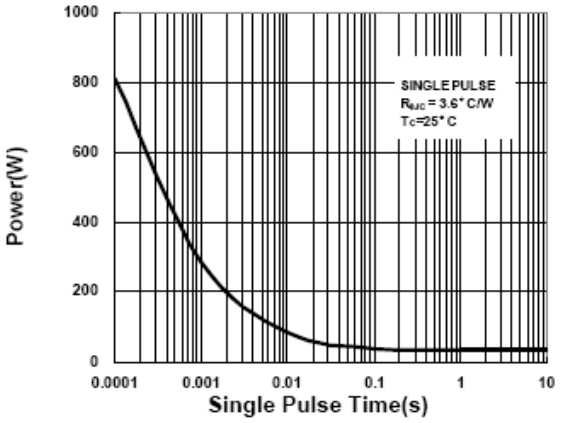
Body Diode Forward Voltage VS Source current



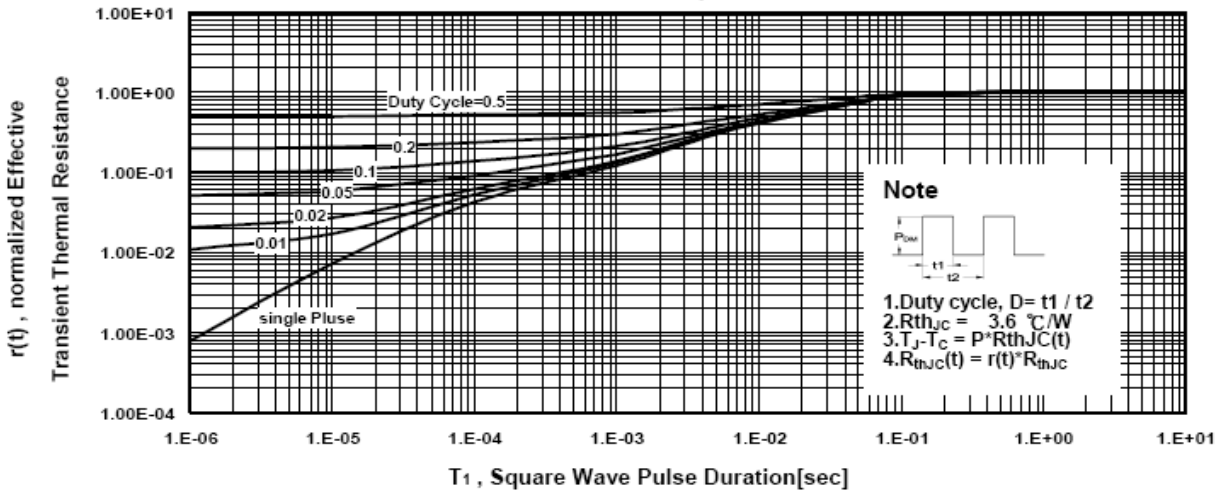
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



UNIKC Semiconductor

RoHS Compliant

P9006ETF

P-Channel Enhancement Mode MOSFET

Package Dimension

TO-220F (3-Lead) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.2		4.93	e	2.05	2.55	3.05
A1	2.34		3.1	F	27.45		30.6
B	17.77		20.3	G	7.72		9.3
b	0.6		1.05	H	6.1		7.1
b1	0.9	1.23	1.62	L	12.5		14.5
b2	0.6		1.9	L1	1.97		3.8
c	0.4		1.0	P	2.98		3.4
D	14.7		16.4	Q	2.1		2.96
D1	6.4		7.5	q	3.0		3.8
E	9.7		10.4